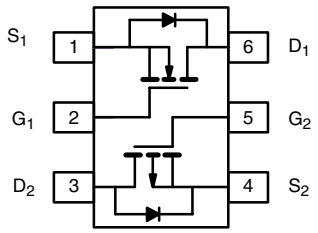
Complementary N- and P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (mA)
N-Channel	20	5 at V_{GS} = 4.5 V	200
		7 at V_{GS} = 2.5 V	175
		9 at V_{GS} = 1.8 V	150
		10 at V_{GS} = 1.5 V	50
P-Channel	- 20	8 at V_{GS} = - 4.5 V	- 150
		12 at V_{GS} = - 2.5 V	- 125
		15 at V_{GS} = - 1.8 V	- 100
		20 at V_{GS} = - 1.5 V	- 30

SC-89



Top View

Marking Code: M

Ordering Information: Si1035X-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET: 1.5 V Rated
- Very Small Footprint
- High-Side Switching
- Low On-Resistance:
  N-Channel, 5 Ω
  P-Channel, 8 Ω
- Low Threshold: ± 0.9 V (typ.)
- Fast Switching Speed: 45 ns (typ.)
- 1.5 V Operation
- Gate-Source ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

APPLICATIONS

- Replace Digital Transistor, Level-Shifter
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	N-Channel		P-Channel		Unit
			5 s	Steady State	5 s	Steady State	
Drain-Source Voltage		V_{DS}	20		- 20		V
Gate-Source Voltage		V_{GS}	± 5				
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	190	180	- 155	- 145	mA
	T_A = 85 °C		140	130	- 110	- 105	
Pulsed Drain Current[b]		I_{DM}	650		- 650		
Continuous Source Current (Diode Conduction)		I_S	450	380	- 450	- 380	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	280	250	280	250	mW
	T_A = 85 °C		145	130	145	130	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150				°C
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000				V

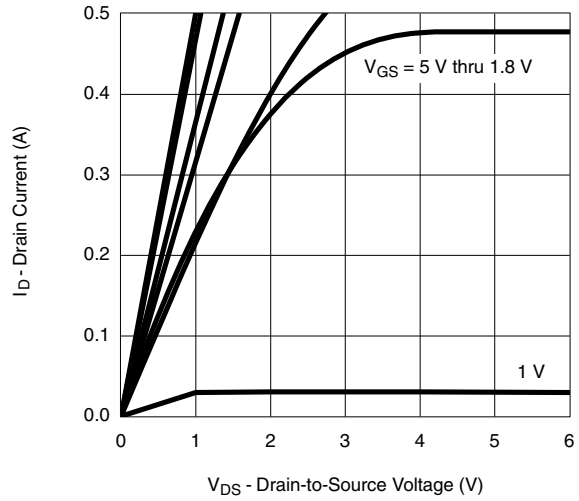
Notes:
a. Surface mounted on FR4 board.
b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.**	**Max.**	**Unit**
Static							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	N-Ch	0.40			V
		V_{DS} = V_{GS}, I_D = - 250 µA	P-Ch	- 0.40			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 2.8 V	N-Ch		± 0.5	± 1.0	µA
			P-Ch		± 0.5	± 1.0	
		V_{DS} = 0 V, V_{GS} = ± 4.5 V	N-Ch		± 1.5	± 3.0	
			P-Ch		± 1.0	± 3.0	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 16 V, V_{GS} = 0 V	N-Ch		1	500	nA
		V_{DS} = - 16 V, V_{GS} = 0 V	P-Ch		- 1	- 500	
		V_{DS} = 16 V, V_{GS} = 0 V, T_J = 85 °C	N-Ch			10	µA
		V_{DS} = - 16 V, V_{GS} = 0 V, T_J = 85 °C	P-Ch			- 10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 4.5 V	N-Ch	250			mA
		V_{DS} = - 5 V, V_{GS} = - 4.5 V	P-Ch	- 200			
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 200 mA	N-Ch			5	Ω
		V_{GS} = - 4.5 V, I_D = - 150 mA	P-Ch			8	
		V_{GS} = 2.5 V, I_D = 175 mA	N-Ch			7	
		V_{GS} = - 2.5 V, I_D = 125 mA	P-Ch			12	
		V_{GS} = 1.8 V, I_D = 150 mA	N-Ch			9	
		V_{GS} = - 1.8 V, I_D = - 100 mA	P-Ch			15	
		V_{DS} = 1.5 V, I_D = 40 mA	N-Ch			10	
		V_{DS} = - 1.5 V, I_D = - 30 mA	P-Ch			20	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 200 mA	N-Ch		0.5		S
		V_{DS} = - 10 V, I_D = - 150 mA	P-Ch		0.4		
Diode Forward Voltage[a]	V_{SD}	I_S = 150 mA, V_{GS} = 0 V	N-Ch			1.2	V
		I_S = - 150 mA, V_{GS} = 0 V	P-Ch			- 1.2	
Dynamic[b]							
Total Gate Charge	Q_g	N-Channel V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 150 mA P-Channel V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 150 mA	N-Ch		750		pC
			P-Ch		1500		
Gate-Source Charge	Q_{gs}		N-Ch		75		
			P-Ch		150		
Gate-Drain Charge	Q_{gd}		N-Ch		225		
			P-Ch		450		
Turn-On Time	t_{ON}	N-Channel V_{DD} = 10 V, R_L = 47 Ω I_D ≅ 250 mA, V_{GEN} = 4.5 V, R_g = 10 Ω P-Channel V_{DD} = - 10 V, R_L = 65 Ω I_D ≅ - 150 mA, V_{GEN} = - 4.5 V, R_g = 10 Ω	N-Ch			75	ns
			P-Ch			80	
Turn-Off Time	t_{OFF}		N-Ch			75	
			P-Ch			90	

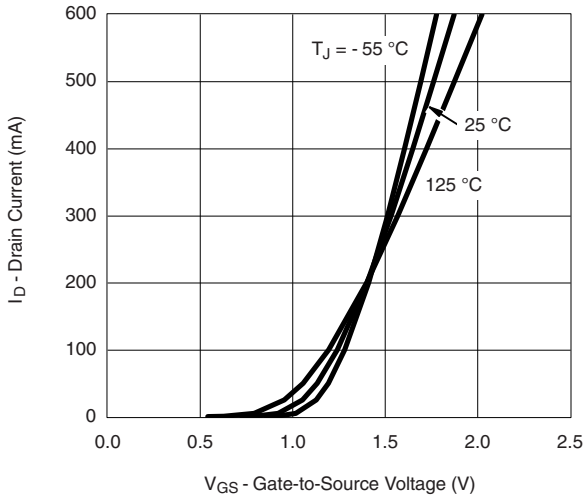
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

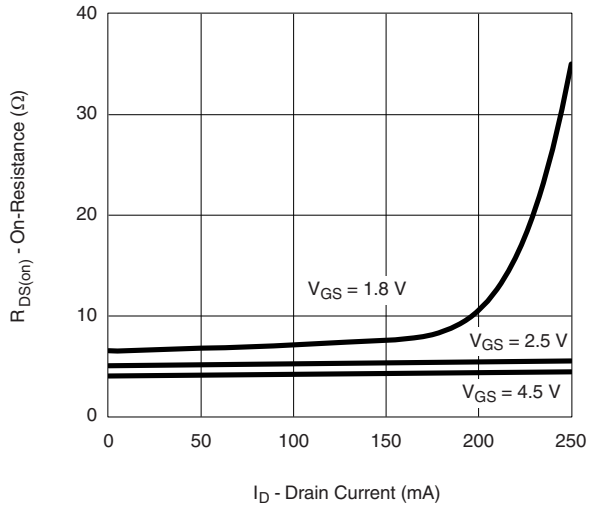
N-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



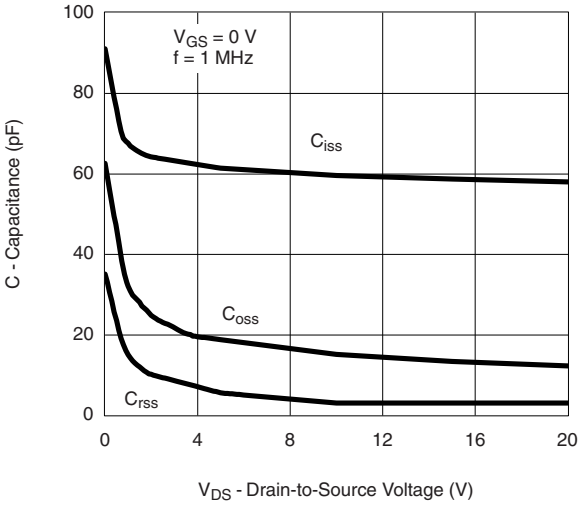
Output Characteristics



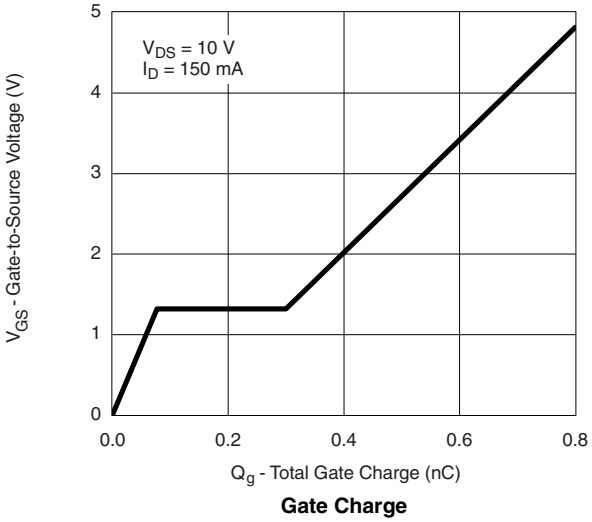
Transfer Characteristics



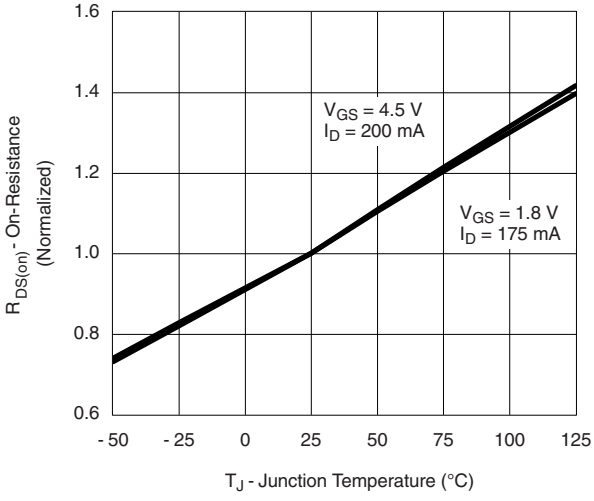
On-Resistance vs. Drain Current



Capacitance

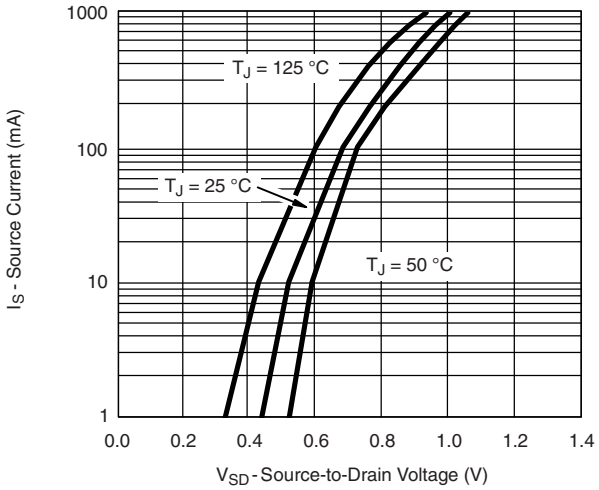


Gate Charge

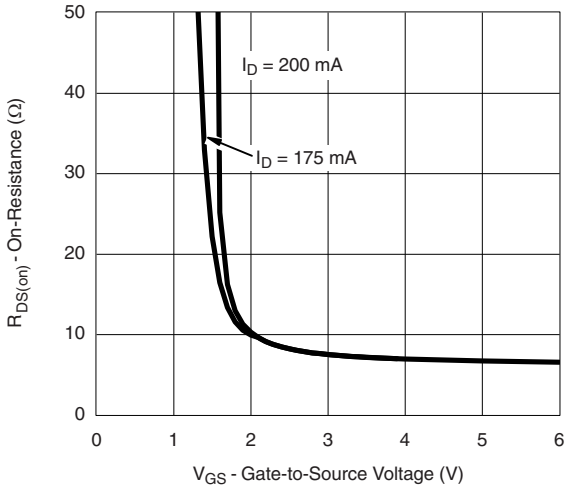


On-Resistance vs. Junction Temperature

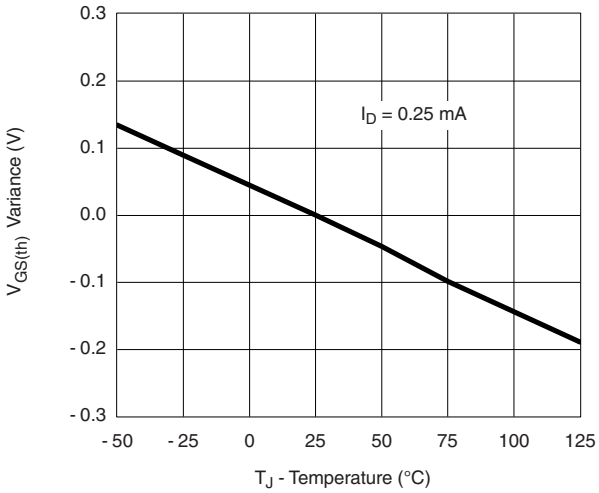
N-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



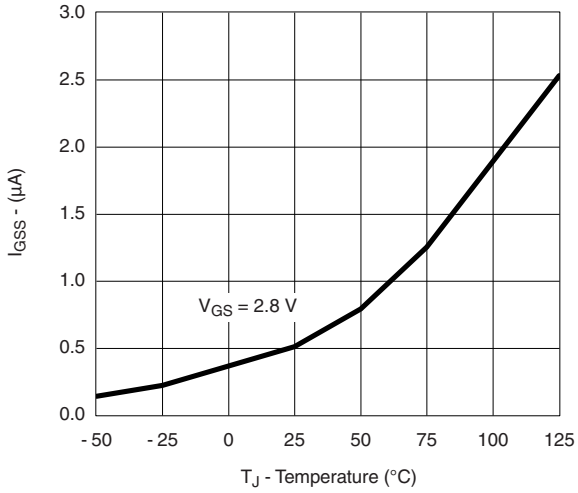
Source-Drain Diode Forward Voltage



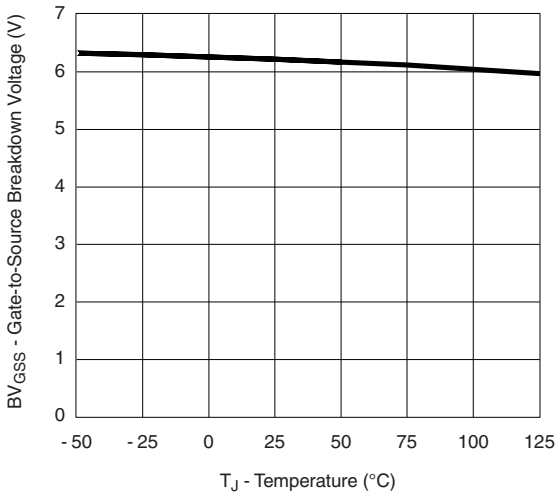
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage Variance vs. Temperature

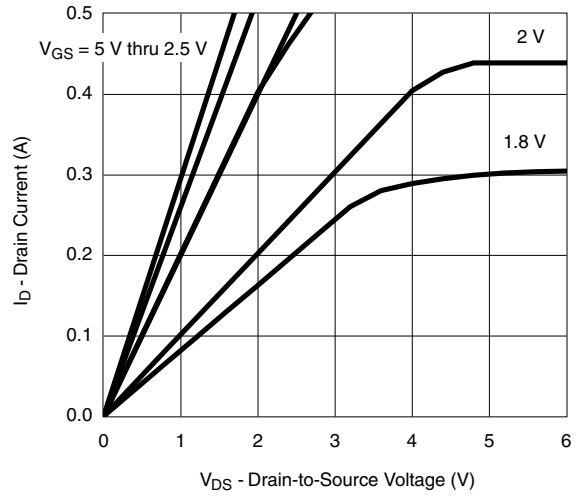


I_{GSS} vs. Temperature

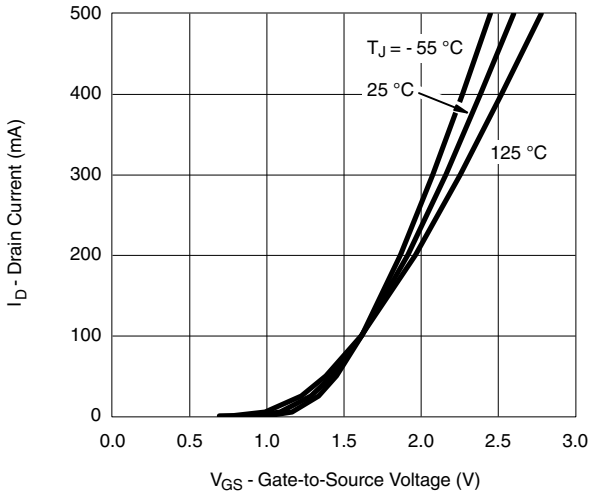


BV_{GSS} vs. Temperature

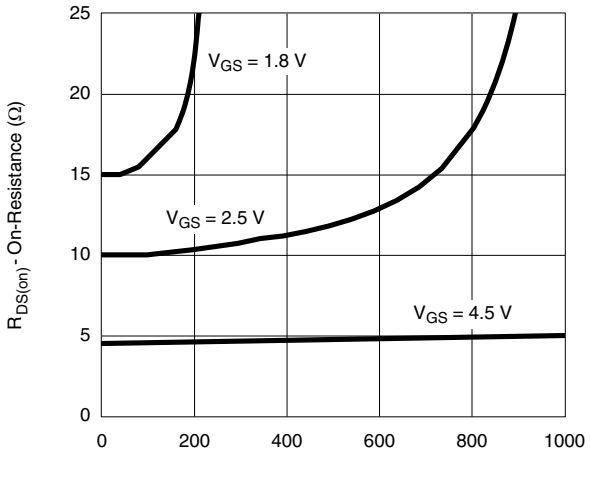
P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



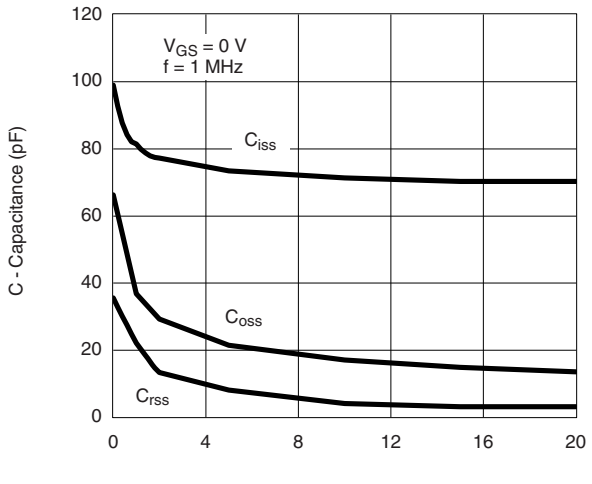
Output Characteristics



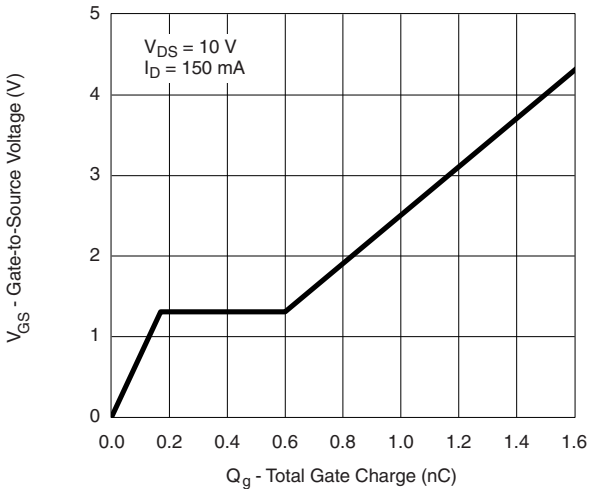
Transfer Characteristics



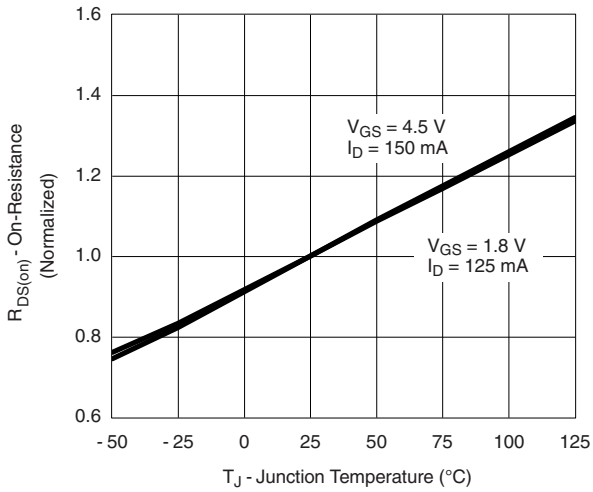
On-Resistance vs. Drain Current



Capacitance

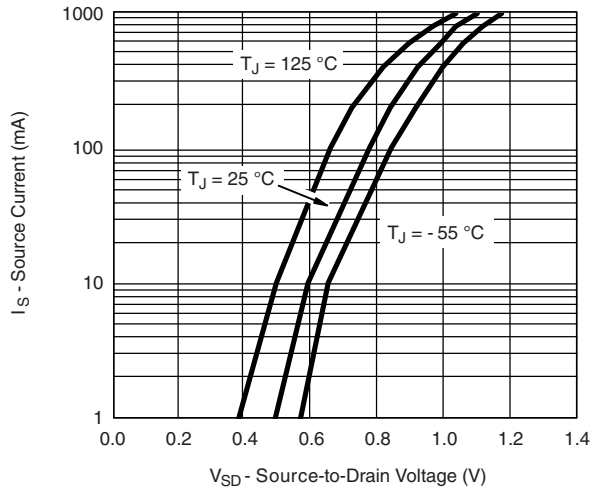


Gate Charge

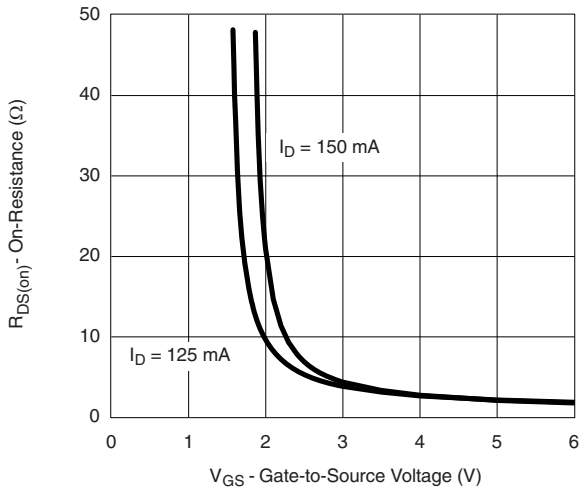


On-Resistance vs. Junction Temperature

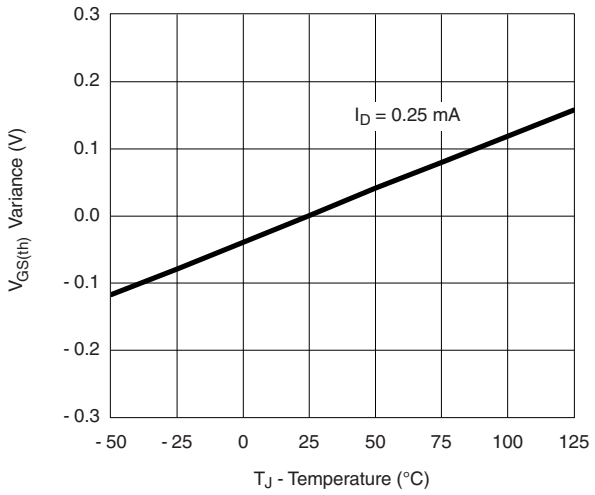
P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



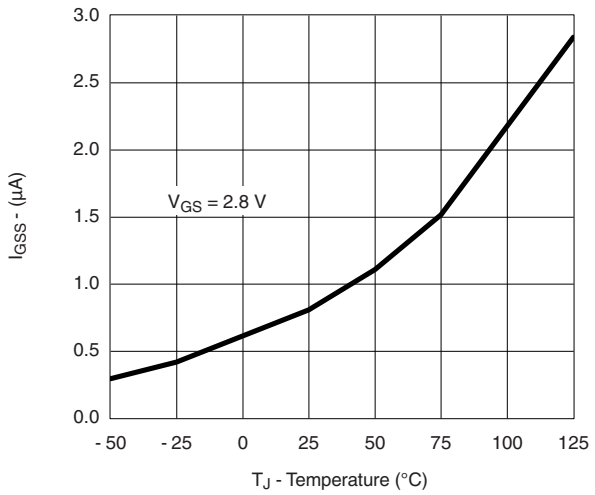
Source-Drain Diode Forward Voltage



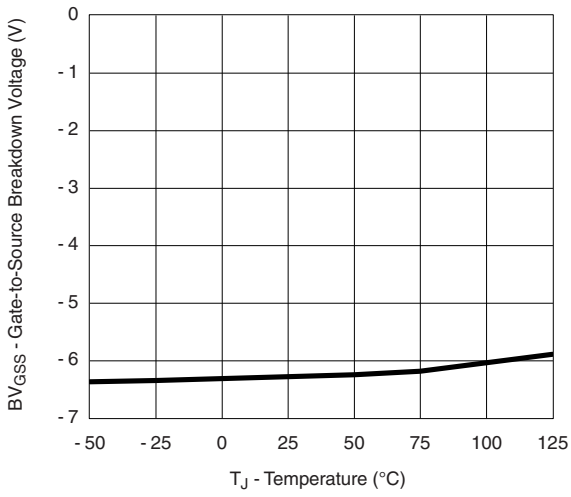
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage Variance vs. Temperature

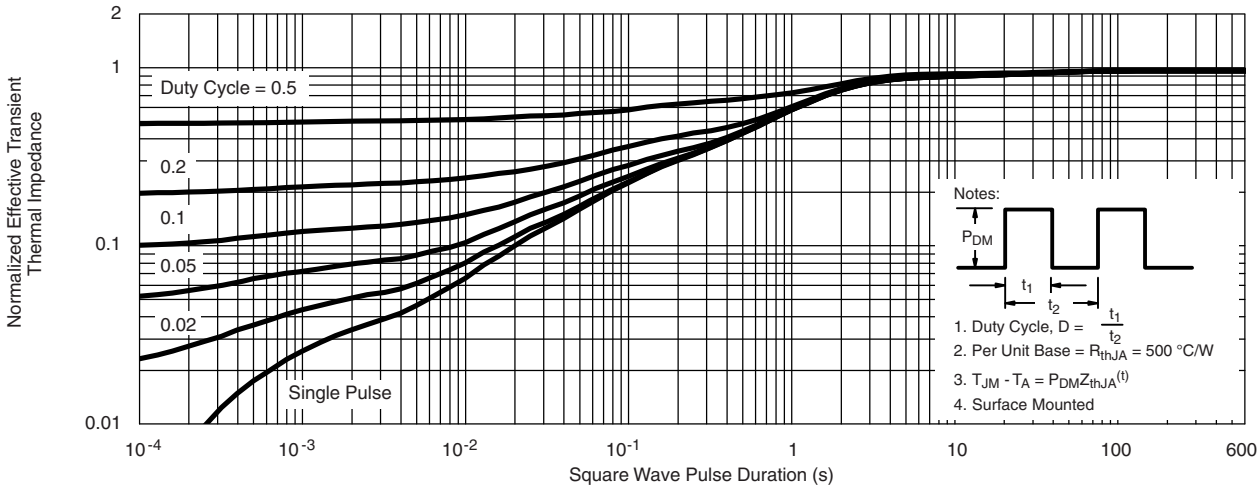


I_{GSS} vs. Temperature



BV_{GSS} vs. Temperature

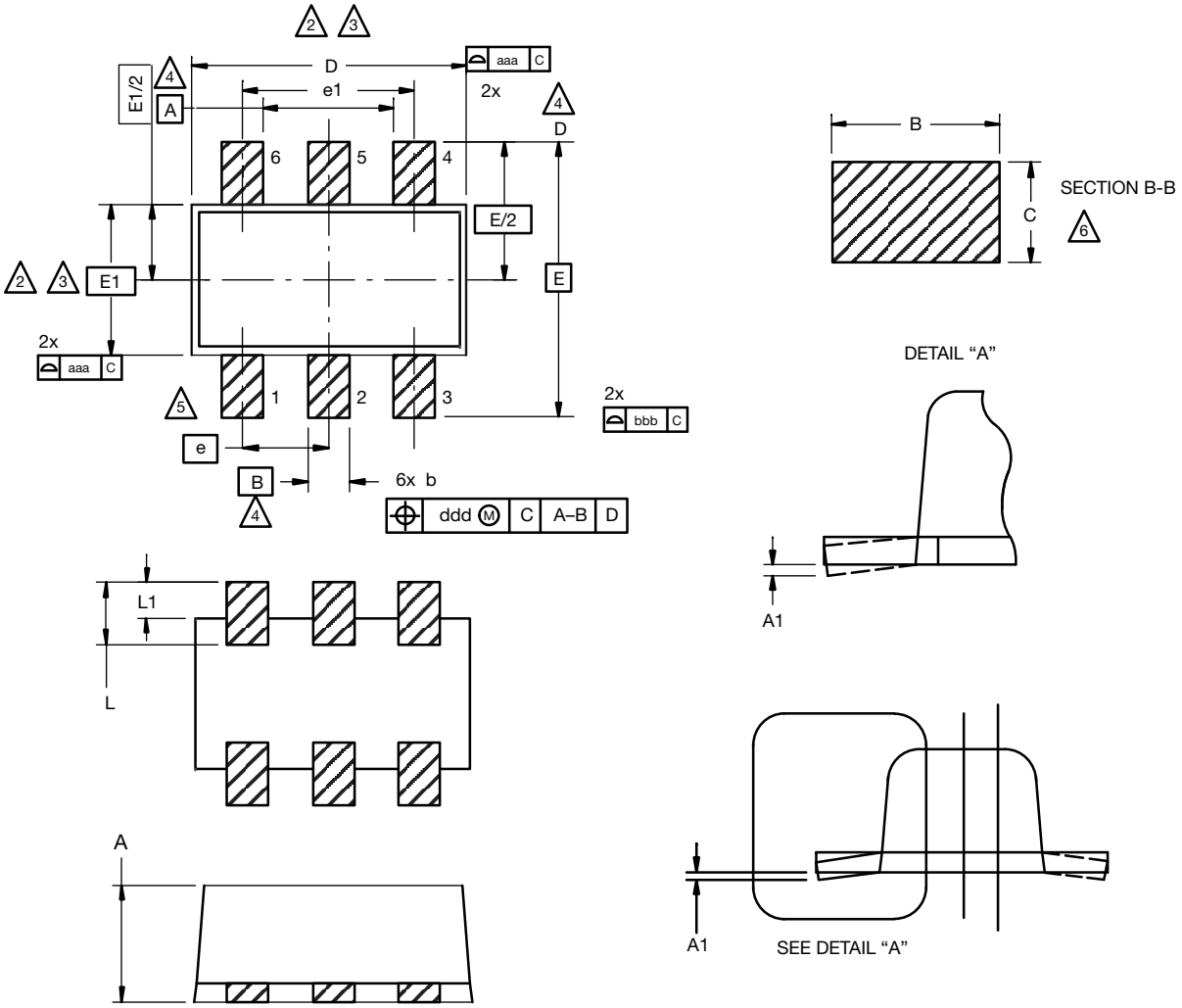
N- OR P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71426.

SC-89 6-Leads (SOT-563F)



Notes

1. Dimensions in millimeters.

2. Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

3. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

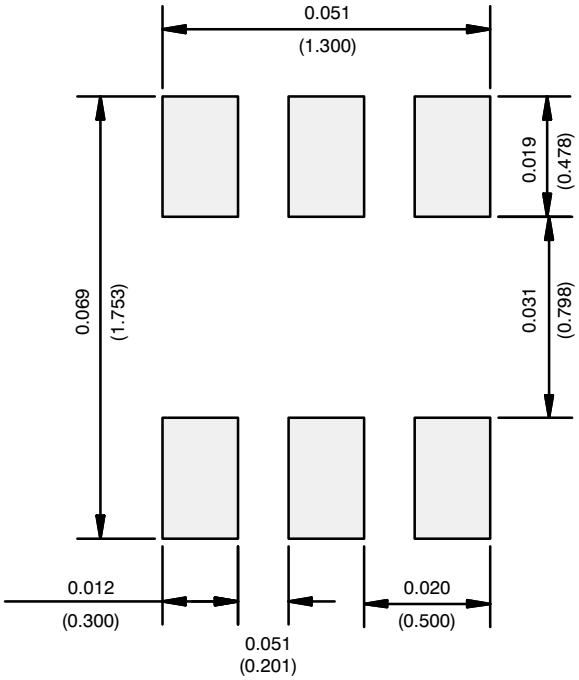
4. Datums A, B and D to be determined 0.10 mm from the lead tip.

5. Terminal numbers are shown for reference only.

6. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.56	0.58	0.60
A1	0	0.02	0.10
b	0.15	0.22	0.30
c	0.10	0.14	0.18
D	1.50	1.60	1.70
E	1.50	1.60	1.70
E1	1.15	1.20	1.25
e	0.45	0.50	0.55
e1	0.95	1.00	1.05
L	0.25	0.35	0.50
L1	0.10	0.20	0.30
C14-0439-Rev. C, 11-Aug-14 DWG: 5880			

RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

Return to Index

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by Vishay ***manufacturer:***

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B